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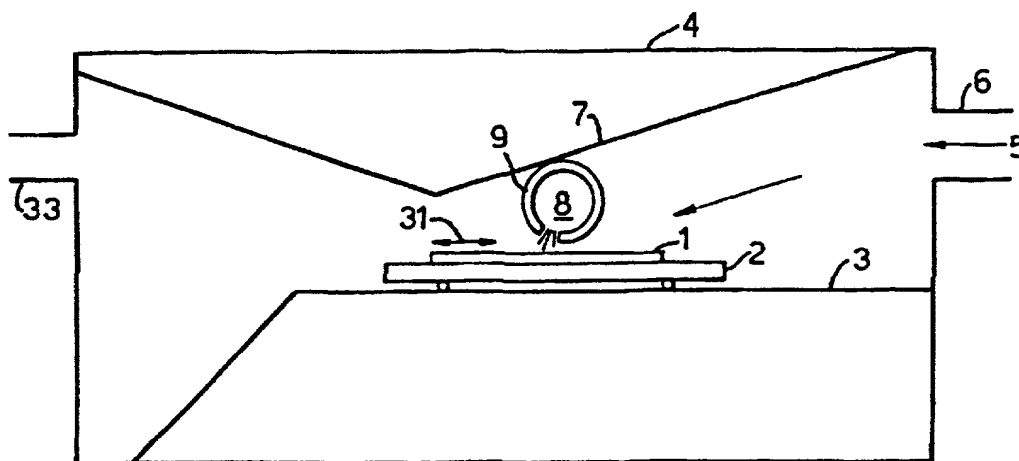
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(54) Title: METHOD AND APPARATUS FOR EPITAXIALLY GROWING A MATERIAL ON A SUBSTRATE



(57) Abstract

A method of epitaxially growing a material on a substrate (1). The method comprises separately heating precursors to their respective decomposition temperatures at or adjacent a region of the substrate to generate species which are supplied separately to the region and which combine at the region.